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AMENDMENTS TO THE CLAIMS:

The following listing of claims replaces all prior listings, and all prior versions, of claims in the application.

Listing Of Claims:

1-29. (Cancelled)

30. (Previously Presented) An abrasive comprising cerium oxide particles, said particles having a crystal grain boundary and having a maximum diameter of not larger than 3000 nm.

31. (Currently Amended) An abrasive comprising cerium oxide particles, wherein a crystallite of said cerium oxide particles having has a crystal grain boundaries boundary and has a maximum diameter not larger than 600 nm.

32. (Currently Amended) The abrasive of Claim 30, wherein said a crystallite of said cerium oxide particles has a maximum diameter of not larger than 600 nm.

33. (Previously Presented) The abrasive of Claim 30, wherein said cerium oxide particles have pores.

34. (Previously Presented) The abrasive of Claim 30, wherein said cerium oxide particles have a porosity of from 10 to 30% as determined from the ratio of a

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true density measured with a pycnometer to a theoretical density determined by X-ray Rietveld analysis.

35. (Previously Presented) The abrasive of Claim 30, wherein said cerium oxide particles have a pore volume of from 0.02 to 0.05cm<sup>3</sup>/g as measured by B.J.H. method.

36. (Previously Presented) The abrasive of Claim 30, wherein said cerium oxide particles have a bulk density not higher than 6.5 g/cm<sup>3</sup>.

37. (Currently Amended) The abrasive of Claim 30, further comprising a medium, wherein said medium is water.

38. (Currently Amended) The abrasive of Claim 30, further comprising a dispersant.

39. (Previously Presented) The abrasive of Claim 38, wherein said dispersant is at least one selected from a water-soluble organic polymer, a water-soluble anionic surfactant, a water-soluble nonionic surfactant and water-soluble amine.

40. (Currently Amended) An abrasive as claimed in claim 39, wherein said dispersant is a polyacrylic acid type polymer.

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41. (Currently Amended) The abrasive of Claim 30, wherein cerium oxide particles with a diameter not smaller than 1 $\mu$ m occupies at least 0.1% by weight of the total weight of the cerium oxide particles.

42. (Previously Presented) The abrasive of Claim 30, wherein said cerium oxide particles having said crystal grain boundary have a property of polishing a target member while collapsing.

43. (Currently Amended) The abrasive of Claim 30, wherein said cerium oxide particles having said crystal grain boundary have a property of polishing a target member while forming new surfaces not coming into contact with said any medium.

44. (Previously Presented) The abrasive of Claim 30, wherein a content of the cerium oxide particles having a particle diameter not smaller than 0.5  $\mu$ m after polishing, measured by centrifugal sedimentation after polishing a predetermined target substrate, is in a ratio of not more than 0.8 with respect to that content before polishing.

45. (Previously Presented) The abrasive of Claim 30, wherein cerium oxide particle diameter at D90% by volume measured by laser diffraction after a target substrate has been polished is in a ratio of from 0.4 to 0.9 with respect to that particle diameter before polishing.

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46. (Previously Presented) A method of polishing a predetermined substrate, comprising polishing said substrate using an abrasive comprising cerium oxide particles, said particles having a crystal grain boundary and having a maximum diameter of not larger than 3000 nm.

47. (Currently Amended) A-The method of polishing a predetermined substrate as claimed in claim 46, wherein strength of the substrate is larger than the breaking strength of grain boundary of the cerium oxide particles.

48. (Currently Amended) The method of polishing the-a predetermined substrate as claimed in claim 46, wherein said predetermined substrate is a semiconductor chip with a silica film formed thereon.

49. (Previously Presented) A manufacturing method of a semiconductor device comprising the step of polishing a semiconductor chip having a silica film formed thereon with an abrasive comprising cerium oxide particles, said particles having a crystal grain boundary and having a maximum diameter of not larger than 3000 nm.